

# Tatsushi Hamaguchi

## List of Publications by Year in descending order

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22  
papers

527  
citations

840776

11  
h-index

888059

17  
g-index

22  
all docs

22  
docs citations

22  
times ranked

322  
citing authors

#	ARTICLE	IF	CITATIONS
1	Narrow Emission of Blue GaN-Based Vertical-Cavity Surface-Emitting Lasers With a Curved Mirror. IEEE Photonics Journal, 2022, 14, 1-5.	2.0	6
2	Mode control in long cavity VCSELs with a curved mirror. , 2022, , .		1
3	Longitudinal mode control in long cavity VCSELs with a curved mirror. Applied Physics Express, 2022, 15, 072009.	2.4	5
4	Impact of oxygen on band structure at the Ni/GaN interface revealed by hard X-ray photoelectron spectroscopy. Applied Physics Letters, 2021, 118, 121603.	3.3	4
5	49â€²: <i>Invited Paper:</i> Blue and Green VCSEL for Fullâ€²Color Display. Digest of Technical Papers SID International Symposium, 2021, 52, 677-679.	0.3	2
6	Narrow Divergence Emission from Blue GaN-based VCSELs with Curved Mirror. IEEJ Transactions on Electronics, Information and Systems, 2021, 141, 1281-1285.	0.2	1
7	Narrow emission of blue GaN-based vertical-cavity surface-emitting lasers with a curved mirror. , 2021, , .		2
8	Room-temperature continuous-wave operation of green vertical-cavity surface-emitting lasers with a curved mirror fabricated on {20âˆ²21} semi-polar GaN. Applied Physics Express, 2020, 13, 041002.	2.4	27
9	Single transverse mode operation of GaN-based vertical-cavity surface-emitting laser with monolithically incorporated curved mirror. Applied Physics Express, 2019, 12, 084003.	2.4	25
10	A review on the latest progress of visible GaN-based VCSELs with lateral confinement by curved dielectric DBR reflector and boron ion implantation. Japanese Journal of Applied Physics, 2019, 58, SC0806.	1.5	36
11	GaN-based Vertical-Cavity Surface-Emitting Lasers Incorporating Dielectric Distributed Bragg Reflectors. Applied Sciences (Switzerland), 2019, 9, 733.	2.5	15
12	Sub-milliampere-threshold continuous wave operation of GaN-based vertical-cavity surface-emitting laser with lateral optical confinement by curved mirror. Applied Physics Express, 2019, 12, 044004.	2.4	30
13	Recent progress in GaN-based vertical-cavity surface-emitting lasers with lateral optical confinement due to an incorporated curved mirror. , 2019, , .		0
14	Incorporation of a Curved Mirror into GaN-Based VCSEL. , 2018, , .		0
15	Lateral optical confinement of GaN-based VCSEL using an atomically smooth monolithic curved mirror. Scientific Reports, 2018, 8, 10350.	3.3	51
16	Recent progress in GaN-based Vertical-Cavity Surface-Emitting Lasers Having Dielectric Distributed Bragg Reflectors. , 2018, , .		0
17	Lateral carrier confinement of GaN-based vertical-cavity surface-emitting diodes using boron ion implantation. Japanese Journal of Applied Physics, 2016, 55, 122101.	1.5	26
18	Milliwattâ€²class GaNâ€²based blue verticalâ€²cavity surfaceâ€²emitting lasers fabricated by epitaxial lateral overgrowth. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1170-1176.	1.8	65

#	ARTICLE	IF	CITATIONS
19	Continuous wave operation of high power GaN-based blue vertical-cavity surface-emitting lasers using epitaxial lateral overgrowth. Proceedings of SPIE, 2016, , .	0.8	3
20	Room-temperature continuous-wave operation of GaN-based vertical-cavity surface-emitting lasers fabricated using epitaxial lateral overgrowth. Applied Physics Express, 2015, 8, 062702.	2.4	75
21	High-Power (over 100 mW) Green Laser Diodes on Semipolar $\{20\bar{a}r\{2\}1\}$ GaN Substrates Operating at Wavelengths beyond 530 nm. Applied Physics Express, 2012, 5, 082102.	2.4	110
22	Long-Lifetime True Green Laser Diodes with Output Power over 50 mW above 525 nm Grown on Semipolar $\{20\bar{a}r\{2\}1\}$ GaN Substrates. Applied Physics Express, 2012, 5, 082103.	2.4	43